

YJ Planar Schottky Barrier Diode Die Specification

100V 100A, 250mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB250H100AS-290A

Main Products Characterstics

Maximum Ratings

Symbol	Value
I_F	100 A
V_R	100 V
T_J	175 °C
T_{stg}	250 °C
t_{stg}	1000 h
t_{max}	1000 h

Static Electrical Characteristics (Ta = 25°C)

Symbol	Value
I_F	100 A
V_F	≤ 2%
I_R	100 A
V_R	100 V
I_{FS}	100 A
V_{FS}	≤ 2%
I_{RS}	100 A
V_{RS}	≤ 2%

Device Schematics and Outline Drawing

Die Thickness *